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| INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> | Docket Number (optional) | Application Number |
| | 11030.02 | |
| | Applicant(s) Steve K. Hsia et al. | |
| #2 | Filing Date November 8, 2001 | Group Art Unit 2818 |

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 10/035414
 11/08/01

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|-------------------|-----|-----------------|----------|---------------|-------|----------|----------------------------|
| HMS | A | 5,060,195 | 10/22/91 | Gill et al. | | | |
| | B | 5,418,741 | 05/23/95 | Gill | | | |
| | C | 5,487,033 | 01/23/96 | Keeney et al. | | | |
| | D | 5,546,340 | 08/13/96 | Hu et al. | | | |
| | E | 5,553,020 | 09/03/96 | Keeney et al. | | | |
| | F | 5,646,886 | 07/08/97 | Brahmbhatt | | | |
| | G | 5,659,504 | 08/19/97 | Bude et al. | | | |
| | H | 5,959,892 | 09/28/99 | Lin et al. | | | |
| HMS | I | 6,175,519 | 01/16/01 | Lu et al. | | | |

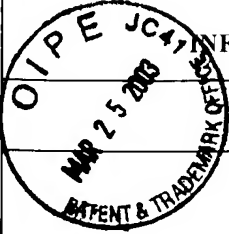
FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
|--|-----|-----------------|------|---------|-------|----------|-------------|----|
| | | | | | | | YES | NO |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|----------|-------|---|
| HMS | J | J. D. Bude et al.; <u>Monte Carlo Simulation of the CHISEL Flash Memory Cell</u> ; IEEE Transactions on Electron Devices, Vol. 47, No. 10, October 2000; p. 1873-1881 |
| HMS | K | J.D. Bude et al.; <u>EEPROM/Flash Sub 5.0V Drain-Source Bias Hot Carrier Writing</u> , IEDM Technical Digest, 1995, p. 989-991 |
| HMS | L | J.D. Bude et al.; <u>Secondary Electron Flash - a High Performance, Low Power Flash Technology for 0.35 μm and Below</u> ; IEDM Technical Digest, 1997, p. 279-282 |
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| EXAMINER | H. Hc | DATE CONSIDERED 5/7/03 |

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|---|-----------------|---|
| HMP | M | Brown, William D. and Brewer, Joe E., eds., Nonvolatile Semiconductor Memory Technology: A Comprehensive Guide to Understanding and Using NVSM Devices, IEEE Press, New York, 1998, pp. 69, 105, 107-108, 203, 213-217, 226-227, 235, 239-241, 244, 247, 279-281. |
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